

What is claimed is:

1. A method of polishing and then cleaning a substrate, comprising:
polishing a substrate by pressing said substrate against a polishing surface; then
5 primarily cleaning said substrate in at least one of two first cleaning units; and then
secondarily cleaning said substrate in a common second cleaning unit, wherein said
common second cleaning unit is constructed and arranged to receive a substrate from each
of said two first cleaning units.

10 2. The method according to claim 1, wherein
primarily cleaning said substrate comprises primarily cleaning said substrate in each
of said two first cleaning units.

15 3. The method according to claim 2, wherein
primarily cleaning said substrate in each of said two first cleaning units comprises
cleaning said substrate in each of said two first cleaning units by subjecting said substrate
to the same cleaning function in said each of said two first cleaning units.

20 4. The method according to claim 2, further comprising:
drying said substrate after secondarily cleaning said substrate.

25 5. The method according to claim 2, wherein
primarily cleaning said substrate comprises supplying an etching liquid to said
substrate, or
secondarily cleaning said substrate comprises supplying an etching liquid to said
substrate.

6. The method according to claim 2, wherein

primarily cleaning said substrate in each of said two first cleaning units comprises
primarily cleaning said substrate in each of said two first cleaning units for a time period that
is greater than a time period for which said substrate is secondarily cleaned in said common
5 second cleaning unit.

7. The method according to claim 2, wherein

primarily cleaning said substrate comprises using ionic water, ozone water, or
hydrogenated water as a cleaning liquid, or

10 secondarily cleaning said substrate comprises using ionic water, ozone water, or
hydrogenated water as a cleaning liquid.

8. The method according to claim 2, wherein

primarily cleaning said substrate in each of said two first cleaning units comprises
15 primarily cleaning said substrate in each of two first cleaning units that are arranged parallel
to one another.

9. The method according to claim 1, further comprising:

20 polishing another substrate by pressing said another substrate against a polishing
surface; then

primarily cleaning said another substrate in a first of said two first cleaning units; and
then

secondarily cleaning said another substrate in said common second cleaning unit,
wherein

25 primarily cleaning said substrate in at least one of said two first cleaning units
comprises primarily cleaning said substrate in a second of said two first cleaning units.

10. The method according to claim 9, wherein
primarily cleaning said substrate in said second of said two first cleaning units
comprises cleaning said substrate in said second of said two first cleaning units by subjecting
said substrate to a first cleaning function, and

5 primarily cleaning said another substrate in said first of said two first cleaning units
comprises cleaning said another substrate in said first of said two first cleaning units by
subjecting said another substrate to a second cleaning function that is the same as said first
cleaning function.

10 11. The method according to claim 9, further comprising:
drying said substrate and said another substrate after secondarily cleaning said
substrate and said another substrate.

12. The method according to claim 9, wherein
15 primarily cleaning said substrate and said another substrate comprises supplying an
etching liquid to said substrate and said another substrate, or
secondarily cleaning said substrate and said another substrate comprises supplying an
etching liquid to said substrate and said another substrate.

20 13. The method according to claim 9, wherein
primarily cleaning said substrate in said second of said two first cleaning units
comprises primarily cleaning said substrate in said second of said two first cleaning units for
a time period that is greater than a time period for which said substrate is secondarily cleaned
in said common second cleaning unit, and

25 primarily cleaning said another substrate in said first of said two first cleaning units
comprises primarily cleaning said another substrate in said first of said two first cleaning
units for a time period that is greater than a time period for which said another substrate is
secondarily cleaned in said common second cleaning unit.

14. The method according to claim 9, wherein
primarily cleaning said substrate and said another substrate comprises using ionic
water, ozone water, or hydrogenated water as a cleaning liquid, or
secondarily cleaning said substrate and said another substrate comprises using ionic
5 water, ozone water, or hydrogenated water as a cleaning liquid.

15. The method according to claim 9, wherein
primarily cleaning said substrate and primarily cleaning said another substrate
comprises primarily cleaning said substrate in parallel with primarily cleaning said another
10 substrate.

16. The method according to claim 1, wherein
primarily cleaning said substrate in at least one of said two first cleaning units
comprises cleaning said substrate in said at least one of said two first cleaning units by
15 subjecting said substrate to a cleaning function that is the same as a cleaning function to be
performed in the other of said two first cleaning units.

17. The method according to claim 1, further comprising:
drying said substrate after secondarily cleaning said substrate.

18. The method according to claim 1, wherein
primarily cleaning said substrate comprises supplying an etching liquid to said
substrate, or
secondarily cleaning said substrate comprises supplying an etching liquid to said
25 substrate.

19. The method according to claim 1, wherein
primarily cleaning said substrate in at least one of said two first cleaning units
comprises primarily cleaning said substrate in said at least one of said two first cleaning units
for a time period that is greater than a time period for which said substrate is secondarily
5 cleaned in said common second cleaning unit.

20. The method according to claim 1, wherein
primarily cleaning said substrate comprises using ionic water, ozone water, or
hydrogenated water as a cleaning liquid, or
10 secondarily cleaning said substrate comprises using ionic water, ozone water, or
hydrogenated water as a cleaning liquid.

21. The method according to claim 1, wherein
primarily cleaning said substrate in at least one of said two first cleaning units
15 comprises primarily cleaning said substrate in at least one of two first cleaning units that are
arranged parallel to one another.